

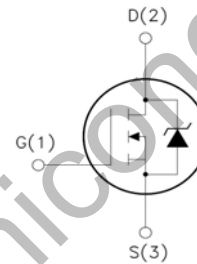


## WGU5N65SE

## Features:

- Low Intrinsic Capacitances.
- Excellent Switching Characteristics.
- Extended Safe Operating Area.
- Unrivalled Gate Charge :Qg=14nC (Typ.).
- BVDSS=650 V, I<sub>D</sub>=5A
- R<sub>DS(on)</sub> : 2.50Ω (Max) @V<sub>G</sub>=10V
- 100% Avalanche Tested

TO-251



1. Gate (G)
2. Drain (D)
3. Source (S)

### Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain-Source Voltage	650	V
I <sub>D</sub>	Drain Current	T <sub>j</sub> =25°C	5.0
		T <sub>j</sub> =100°C	2.7
V <sub>GSS(TH)</sub>	Gate Threshold Voltage	30	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (note1)	120	mJ
I <sub>AR</sub>	Avalanche Current (note2)	5.0	A
P <sub>D</sub>	Power Dissipation (T <sub>j</sub> =25 °C )	50	W
T <sub>j</sub>	Junction Temperature(Max)	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	-	2.4	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient		62.5	°C/W

## Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu A, V_{GS}=0$	650	-	-	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown voltage temperature Coefficient	$I_D=250\mu A$ , Reference to 25°C	-	0.67	-	V/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=650V, V_{GS}=0V$	-	-	10	$\mu A$
		$V_{DS}=520V, T_J=125^\circ C$			100	
$I_{GSSF}$	Gate-body leakage Current, Forward	$V_{GS}=+30V, V_{DS}=0V$	-	-	100	nA
$I_{GSSR}$	Gate-body leakage Current, Reverse	$V_{GS}=-30V, V_{DS}=0V$	-	-	-100	
On Characteristics						
$V_{GS(TH)}$	Gate Threshold Voltage	$I_D=250\mu A, V_{DS}=V_{GS}$	2	-	4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$I_D=2.0A, V_{GS}=10V$	-		2.5	$\Omega$
Dynamic Characteristics						
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0, f=1.0MHz$	-	560	-	$\mu F$
$C_{oss}$	Output Capacitance		-	48	-	
$C_{rss}$	Reverse Transfer Capacitance		-	5.4	-	
Switching Characteristics						
$T_d(on)$	Turn-On Delay Time	$V_{DD}=325V, I_D=5A, R_G=25\Omega$ (Note 3,4)	-	25		nS
$T_r$	Turn-On Rise Time		-	45		
$T_d(off)$	Turn-Off Delay Time		-	25		
$T_f$	Turn-Off Rise Time		-	35		
$Q_g$	Total Gate Charge	$V_{DS}=520V, V_{GS}=10V, I_D=5A$ (Note 3,4)	-	14.3		nC
$Q_{gs}$	Gate-Source Charge		-	2.8	-	
$Q_{gd}$	Gate-Drain Charge		-	4.5	-	
Drain-Source Diode Characteristics and Maximum Ratings						
$I_S$	Max. Diode Forward Current	-		-	4	A
$I_{SM}$	Max. Pulsed Forward Current	-		-	16	
$V_{SD}$	Diode Forward Voltage	$I_D=5A$	-	-	1.4	V
$T_{rr}$	Reverse Recovery Time	$I_S=5A, V_{GS}=0V, diF/dt=100A/\mu s$ (Note 3)	-	393	-	nS
$Q_{rr}$	Reverse Recovery Charge		-	1.5	-	$\mu C$

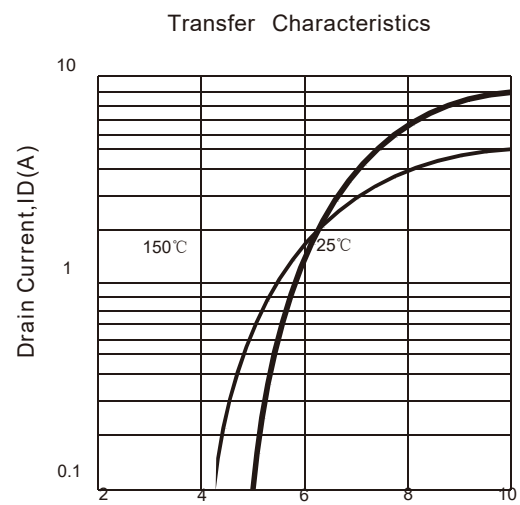
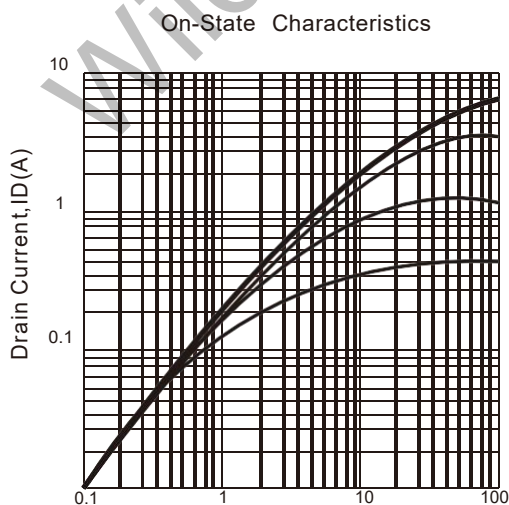
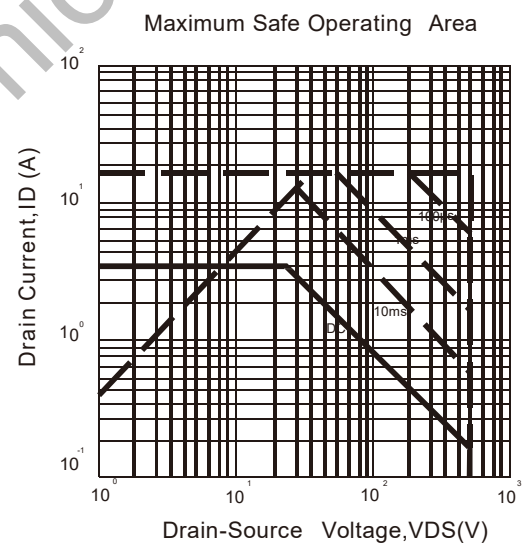
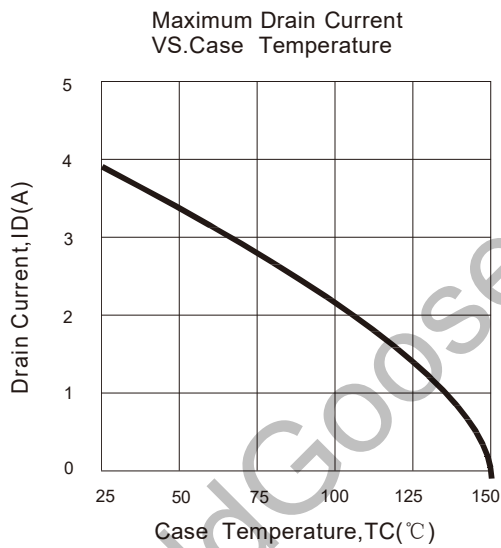
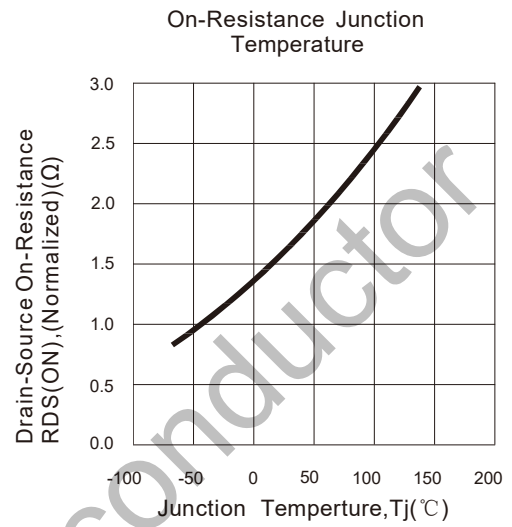
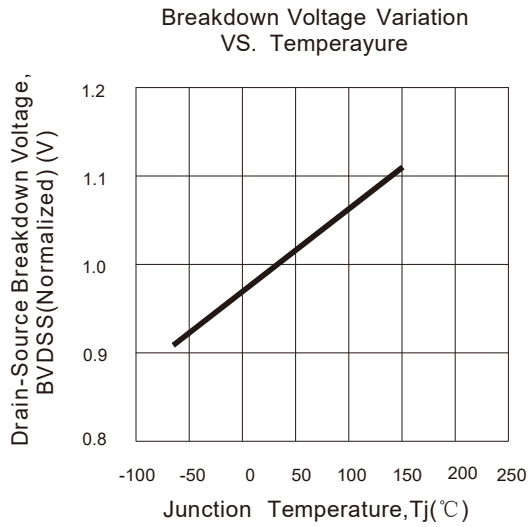
Notes : 1, L=0.5mH, IAS= 5A, VDD=50V, RG=25 $\Omega$ , Starting T<sub>J</sub> =25°C

2, Repetitive Rating : Pulse width limited by maximum junction temperature

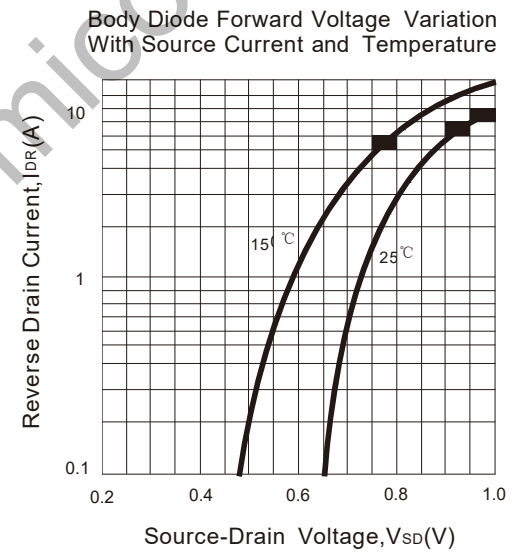
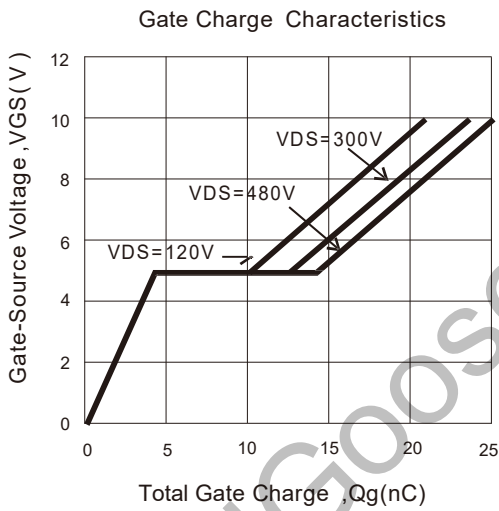
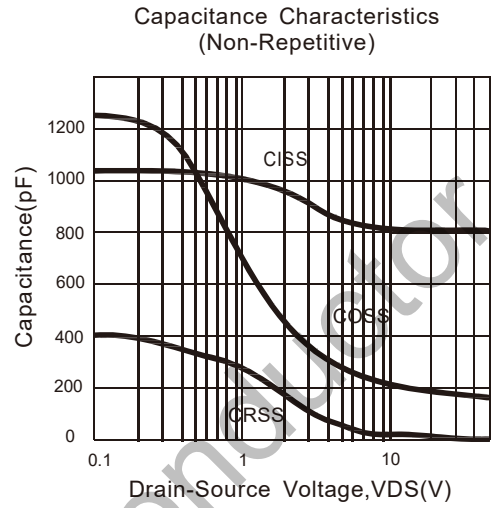
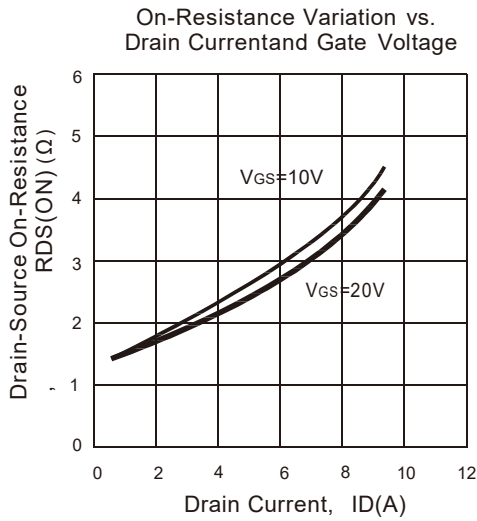
3, Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$

4, Essentially Independent of Operating Temperature

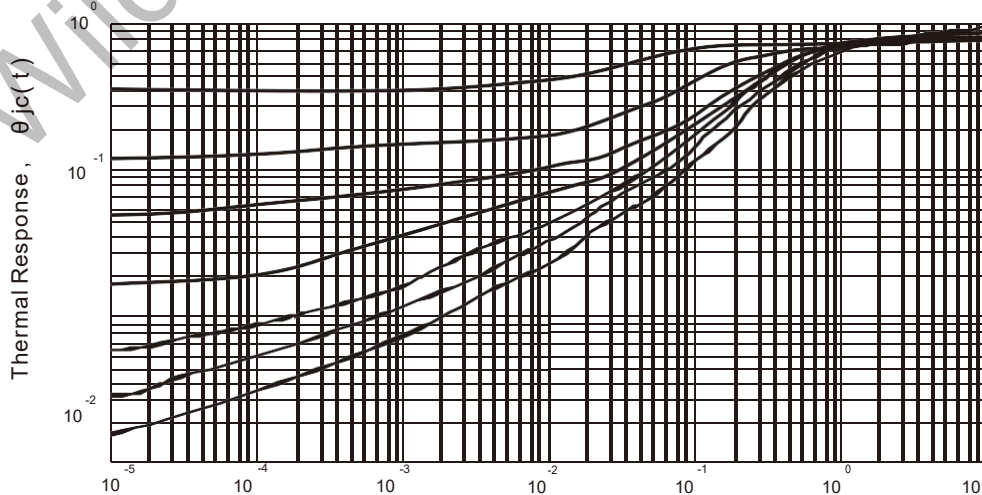
Typical Characteristics



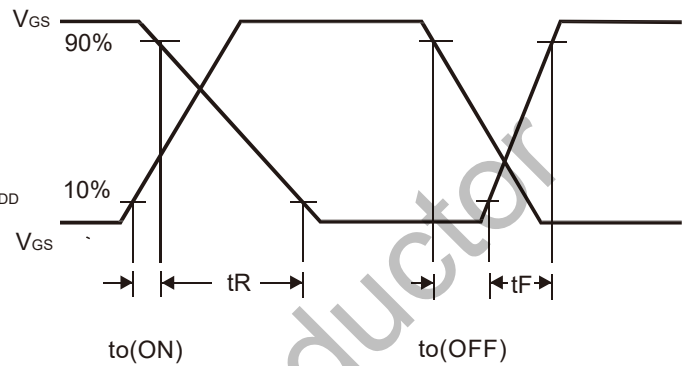
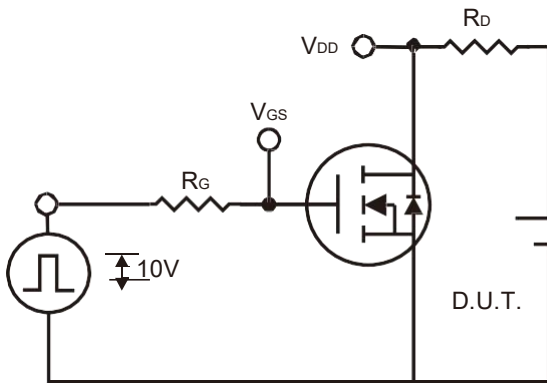
Typical Characteristics (Continued)



Transient Thermal Response Curve

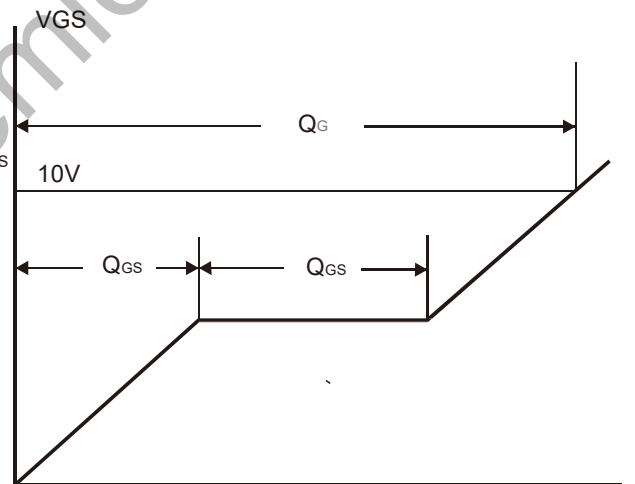
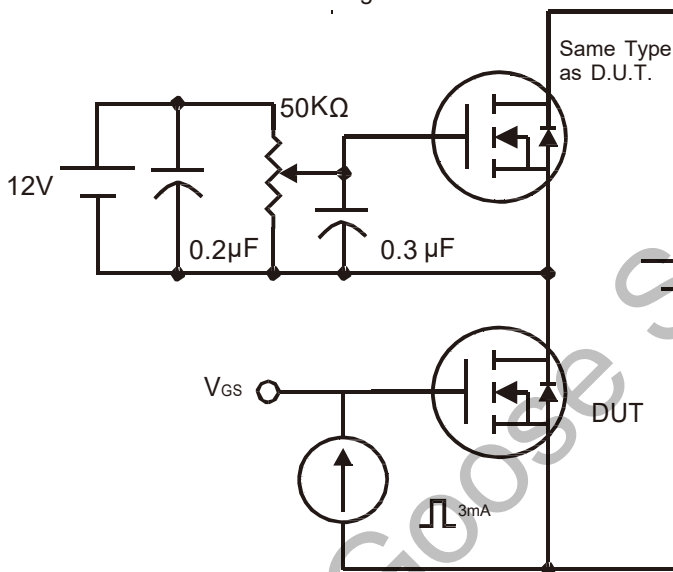


Gate Charge Test Circuit & Waveform



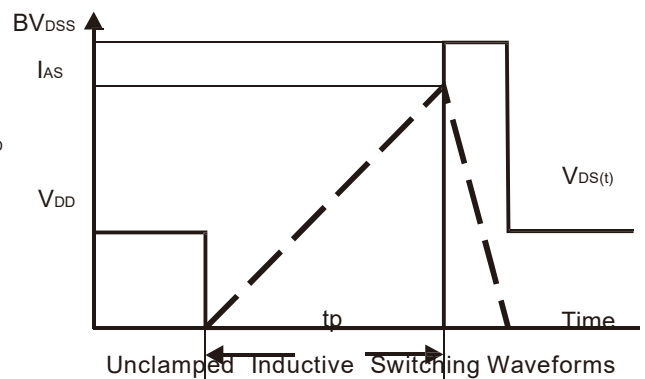
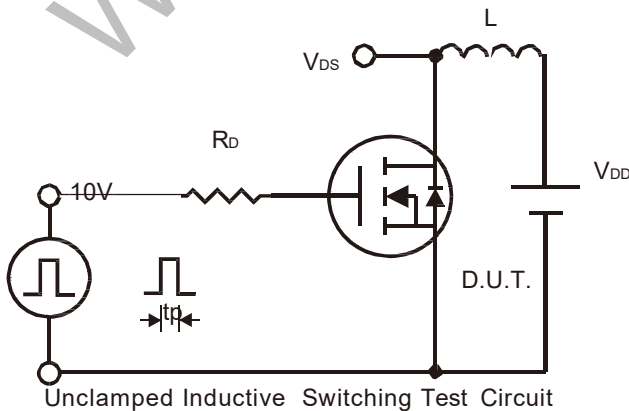
Switching Test Circuit

Switching Waveforms



Gate Charge Test Circuit

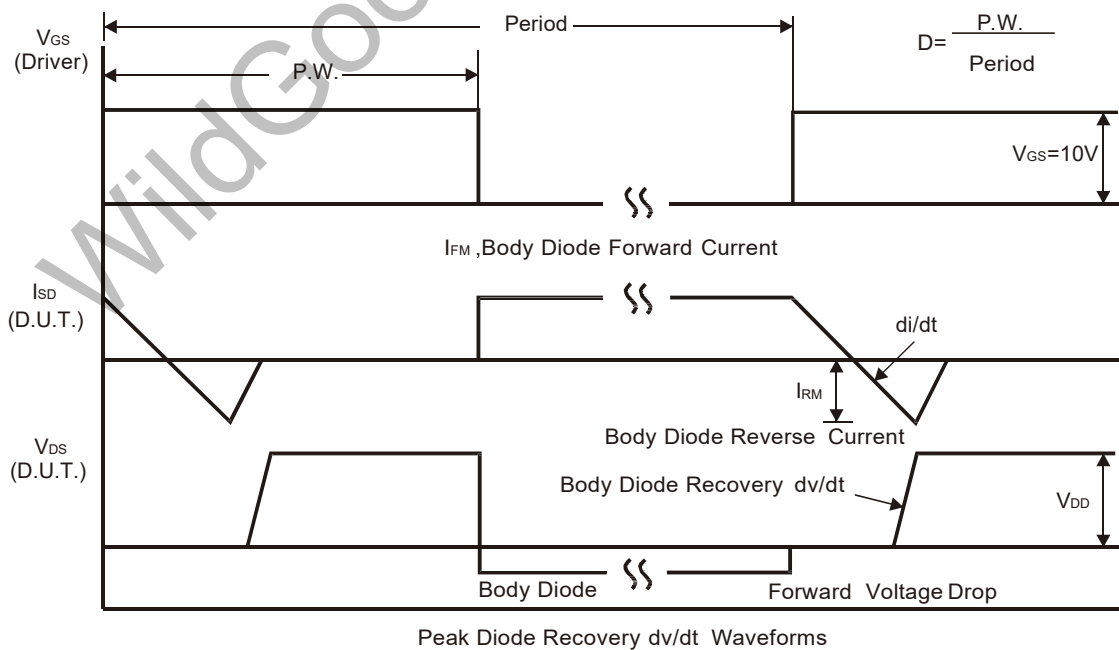
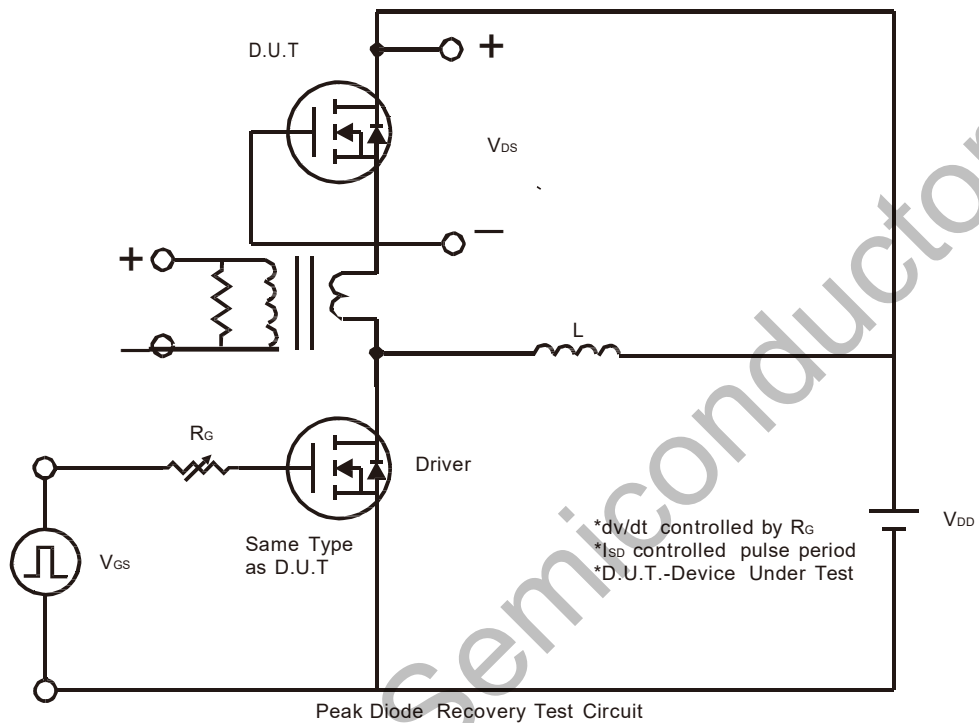
Gate Charge Waveform



Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

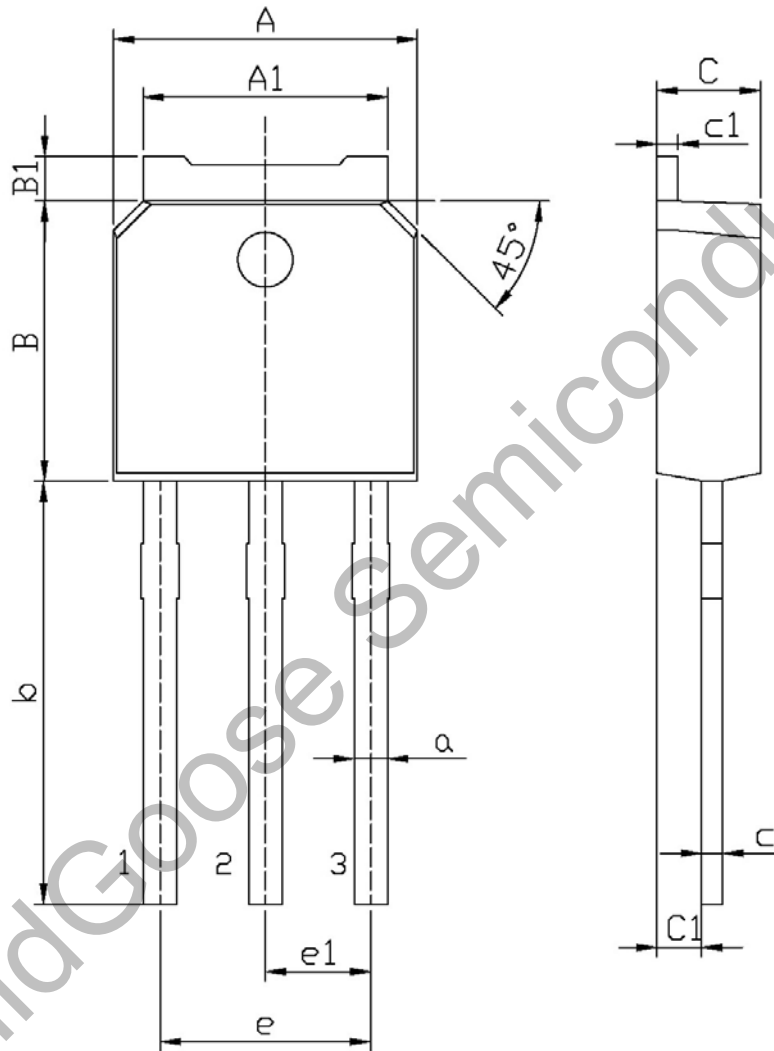
Peak Diode Recovery dv/dt Test Circuit & Waveform



## Package Dimension

T0-251

Unit: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	6.45	6.75	a	0.70	0.90
A1	5.20	5.40	b	9.00	9.40
B	5.95	6.25	c	0.45	0.55
B1	0.95	1.25	c1	0.45	0.55
C	2.20	2.40	e1	2.24	2.34
C1	0.95	1.15	e	4.43	4.73

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Wild Goose](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)  
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)  
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)  
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#) [WMJ80N60C4](#) [BXP2N20L](#)  
[BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP ROG](#) [RQ7L055BGTCR](#) [DMNH15H110SK3-13](#) [SLF10N65ABV2](#)  
[BSO203SP](#) [BSO211P](#) [IPA60R230P6](#) [IPA60R460CE](#)